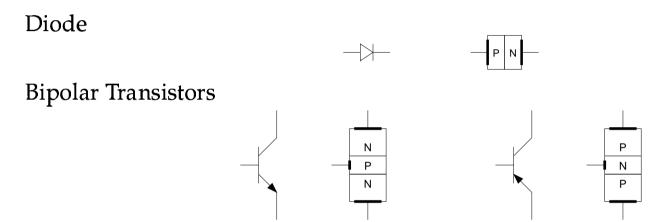
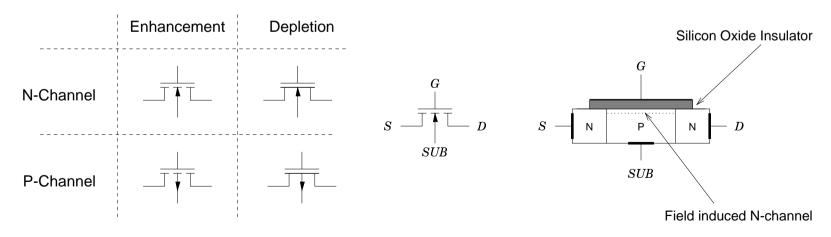
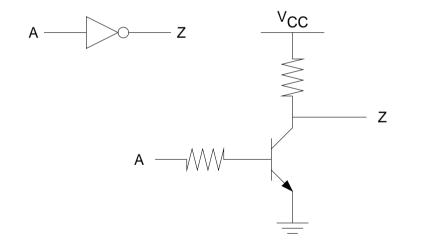
Components for Logic

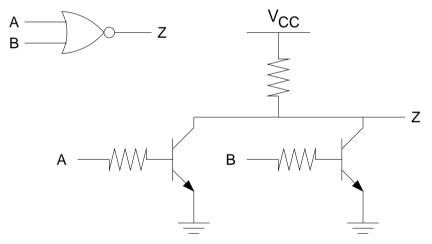


MOS Transistors

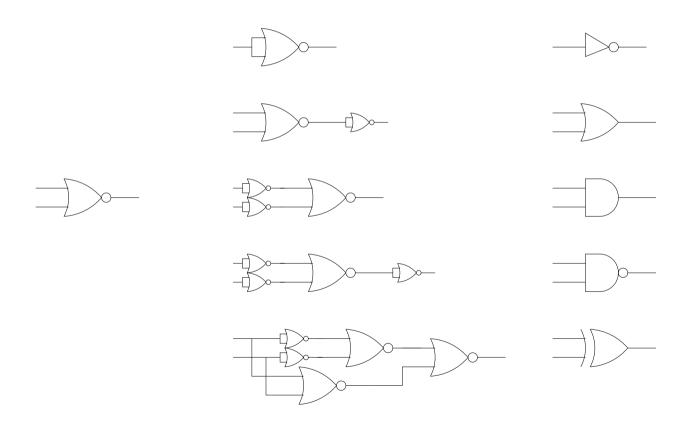


RTL Inverter and NOR gate



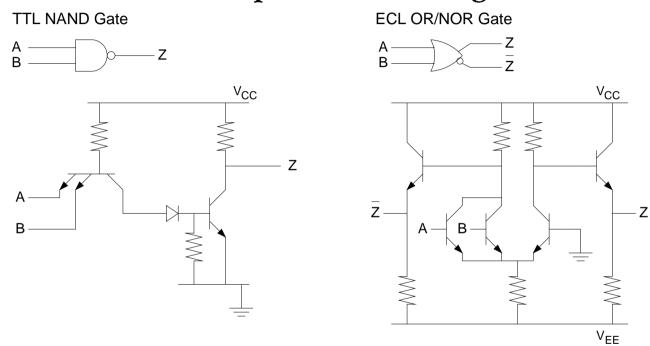


All functions can be realized with a single NOR base gate.¹



¹NAND gates could be used instead.

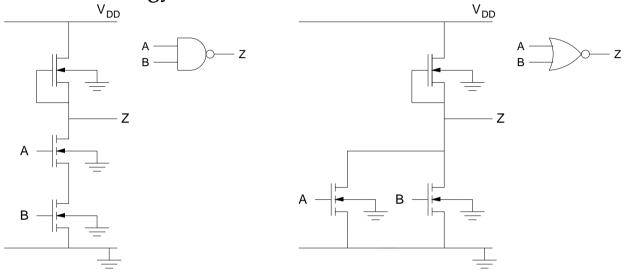
Other Bipolar Technologies



- TTL gives faster switching than RTL at the expense of greater complexity². The characteristic multi-emitter transistor reduces the overall component count.
- ECL is a very high speed, high power, non-saturating technology.

²Most TTL families are more complex than the basic version shown here

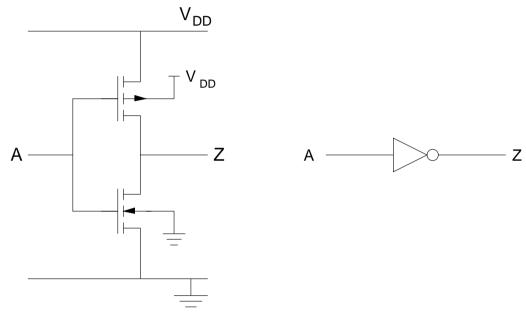
NMOS - a VLSI technology.



- Circuit function determined by series/parallel combination of devices.
- Depletion transistor acts as non-linear load resistor.
 Resistance increases as the enhancement device turns on, thus reducing power consumption.
- The low output voltage is determined by the size ratio of the devices.

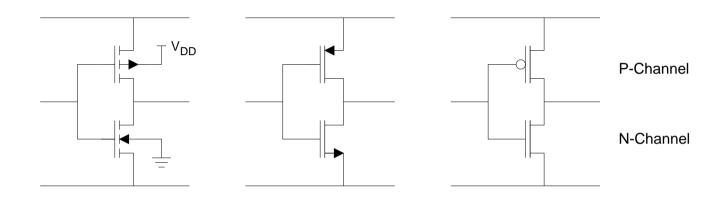
CMOS logic

CMOS - state of the art VLSI.



- An active PMOS device complements the NMOS device giving:
 - rail to rail output swing.
 - negligible static power consumption.

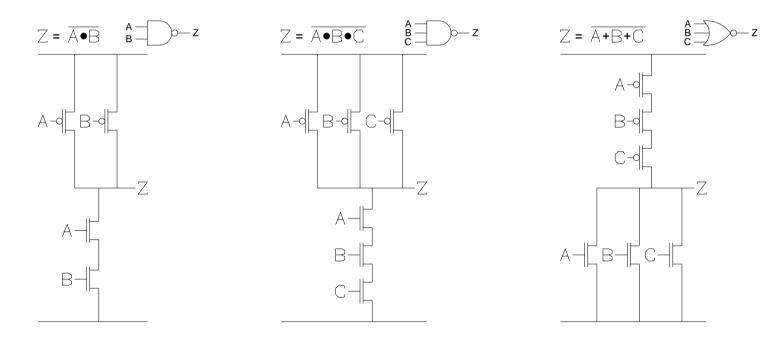
Alternative representations for CMOS transistors



Various shorthands are used for simplifying CMOS circuit diagrams.

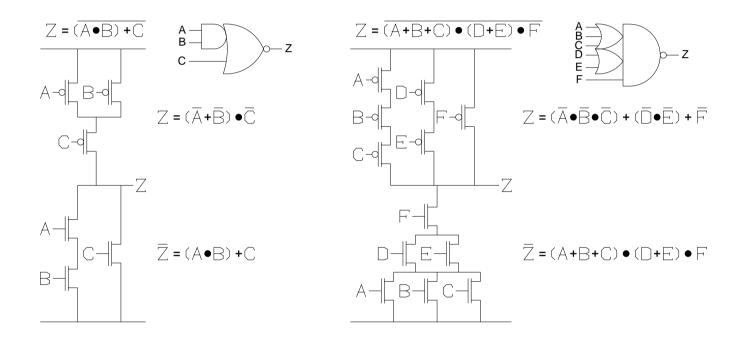
- In general substrate connections are not drawn where they connect to Vdd (PMOS) and Gnd (NMOS).
- All CMOS devices are enhancement mode.
- Transistors act as simple digitally controlled switches.

Static CMOS complementary gates



• For any set of inputs there will exist either a path to Vdd or a path to Gnd.

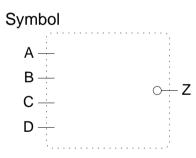
Compound Gates



- All compound gates are inverting.
- Realisable functions are arbitrary AND/OR expressions with inverted output.

Compound Gate Example





Pull Up Network

$$Z = \int (\overline{A}, \overline{B}, \overline{C}, \overline{D})$$

$$Z = \underbrace{ }$$

_____ 7.

 V_{DD}

Pull Down Network

$$\overline{Z} = f(A,B,C,D)$$

 $\overline{Z} = (A \bullet B) + (C \bullet D)$

GND